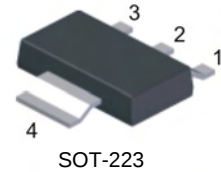
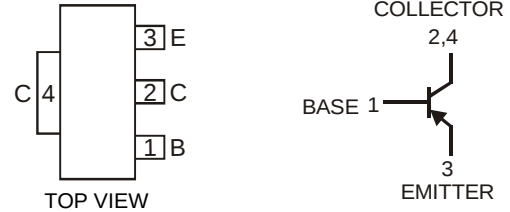


Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)} = 70m\Omega$ at 3A
- High DC Current Gain $h_{FE} > 200$ at $I_C = 2A$
- Complementary NPN Type Available (DNLS320E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT-223



Schematic and Pin Configuration

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish – Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-25	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-3	A
Peak Pulse Current	I_{CM}	-6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 3)	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 1) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-25	-58	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-25	-38	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	-8.5	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	-0.1 10	μA	V _{CB} = -15V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	—	—	-0.1	μA	V _{EB} = -4V, I _C = 0
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.11 -0.20 -0.21	-0.25 -0.45 -0.5	V	I _C = -1A, I _B = -10mA I _C = -2A, I _B = -20mA I _C = -3A, I _B = -100mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-0.8	-1.0	V	I _C = -1A, I _B = -10mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	—	-0.8	—	V	V _{CE} = -2V, I _C = -1A
DC Current Gain	h _{FE}	300 250 200 100	— — — —	800 — — —	—	V _{CE} = -2V, I _C = -10mA V _{CE} = -2V, I _C = -1A V _{CE} = -2V, I _C = -2A V _{CE} = -2V, I _C = -6A
AC CHARACTERISTICS						
Transition Frequency	f _T	100	—	—	MHz	V _{CE} = -5V, I _C = -50mA, f = 30MHz
Input Capacitance	C _{ibo}	—	290	—	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C _{obo}	—	46	—	pF	V _{CB} = -10V, f = 1MHz
Switching Times	t _{on} t _{off}	— —	38 200	— —	ns ns	V _{CC} = -10V, I _C = -500mA, I _{B1} = -I _{B2} = -50mA

Notes: 4. Pulse Test: Pulse width ≤300μs. Duty cycle ≤2.0%.

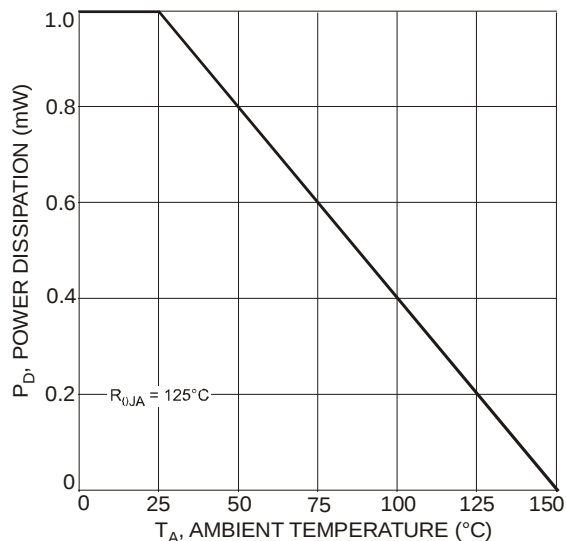


Fig. 1 Max Power Dissipation vs. Ambient Temperature

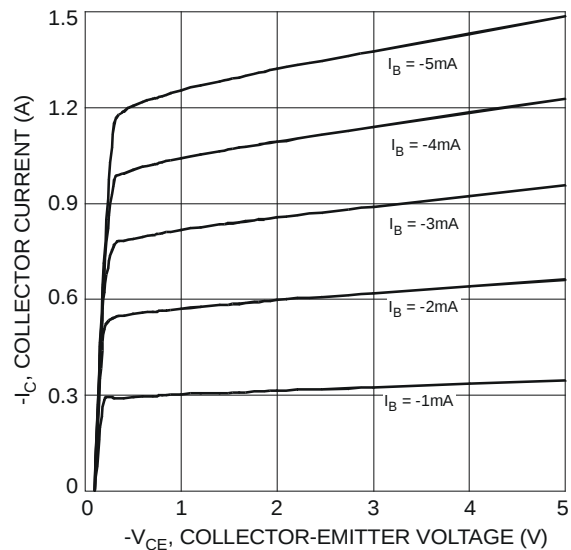


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

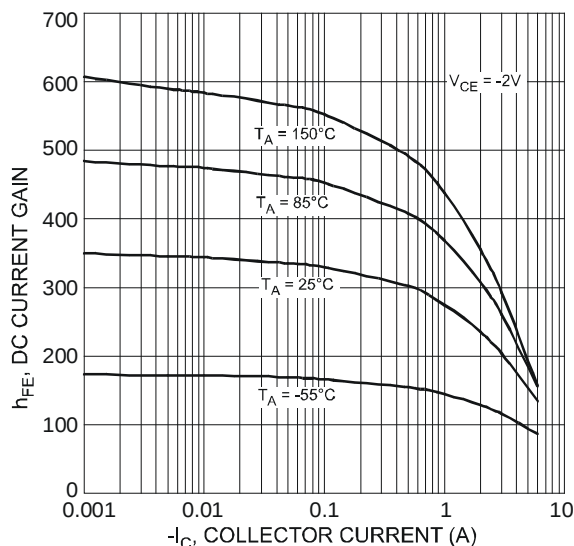


Fig. 3 Typical DC Current Gain vs. Collector Current

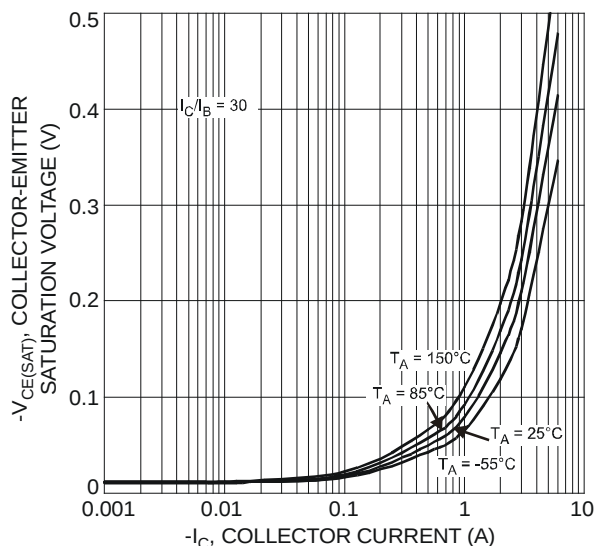


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

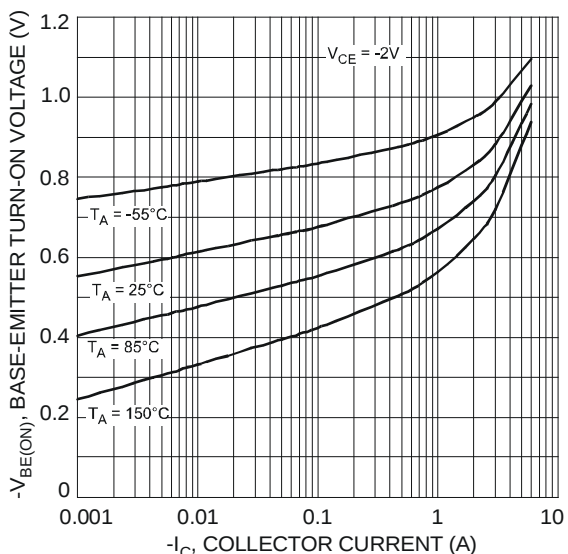


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

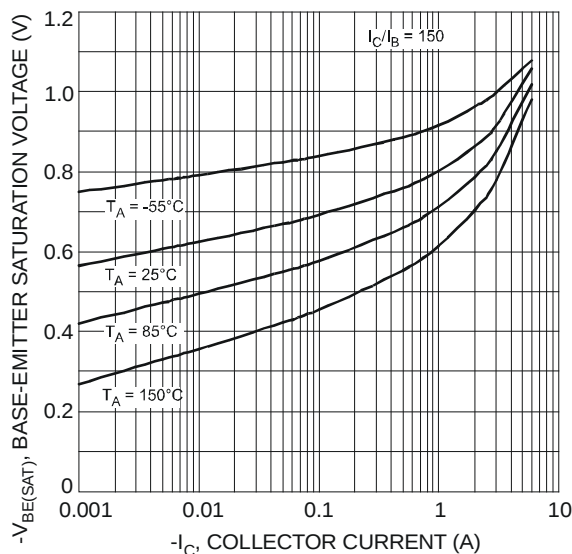


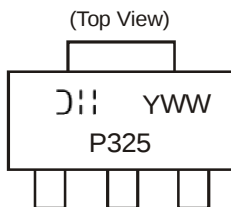
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DPLS325E-13	SOT-223	2500/Tape & Reel

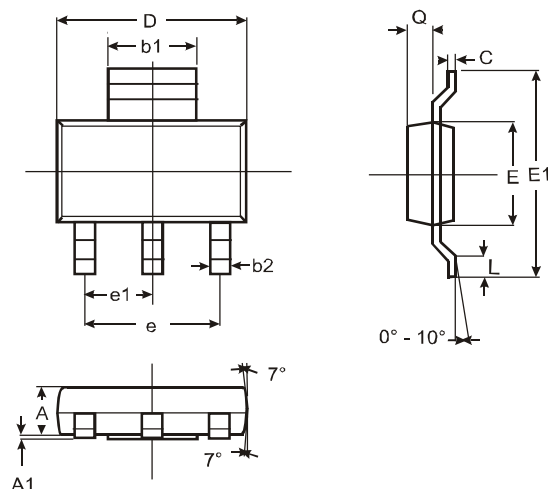
Notes: 5. For packaging details, please go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



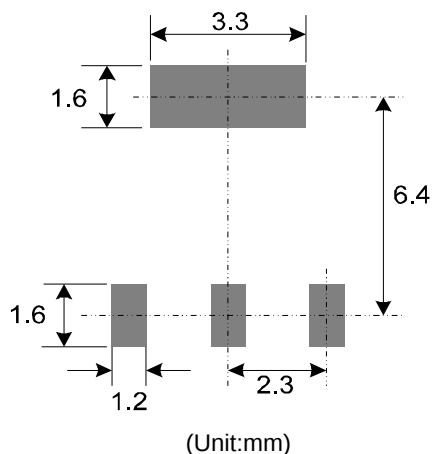
P325 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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